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Inclosure Material:

Metal

Overall Length:

0.320 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

350.0 breakdown voltage, collector-to-base, emitter open and 350.0 breakdown voltage, collector-to-emitter, base open and 8.0

breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

500.00 milliamperes source cutoff current

Power Rating Per Characteristic:

3.5 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius case

Special Features:

Junction pattern arrangement: npn

Test Data Document:

15942-363258 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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